

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max $T_C = +25^\circ C$
30V	5.0m Ω @ $V_{GS} = 10V$	60A
	7.4m Ω @ $V_{GS} = 4.5V$	50A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

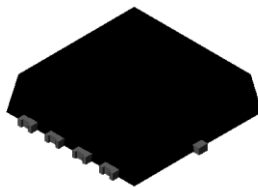
Features and Benefits

- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

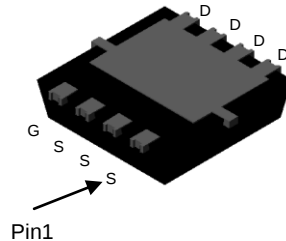
Mechanical Data

- Case: PowerDI[®] 3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208②③
- Weight: 0.072 grams (Approximate)

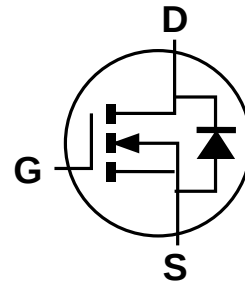
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



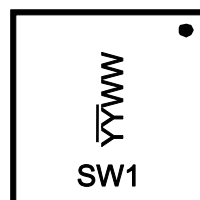
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3009LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMN3009LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



SW1 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digit of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	I _D	60	A
		48	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	90	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	60	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I _{SM}	90	A
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	33	A
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	58	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	126	°C/W
Steady State			
Total Power Dissipation (Note 6)	P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	62	°C/W
Steady State			
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	4.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.5	5.0	mΩ	V _{GS} = 10V, I _D = 30A
		—	4.9	7.4		V _{GS} = 4.5V, I _D = 15A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	2,000	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	315	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	247	—	pF	
Gate Resistance	R _g	—	2.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	20	—	nC	V _{DS} = 15V, I _D = 15A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	42	—	nC	
Gate-Source Charge	Q _{gs}	—	4.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	7.4	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.9	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _G = 3.3Ω, I _D = 15A
Turn-On Rise Time	t _R	—	4.1	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	31	—	ns	
Turn-Off Fall Time	t _F	—	15	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	15	—	ns	I _F = 15A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	6.0	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

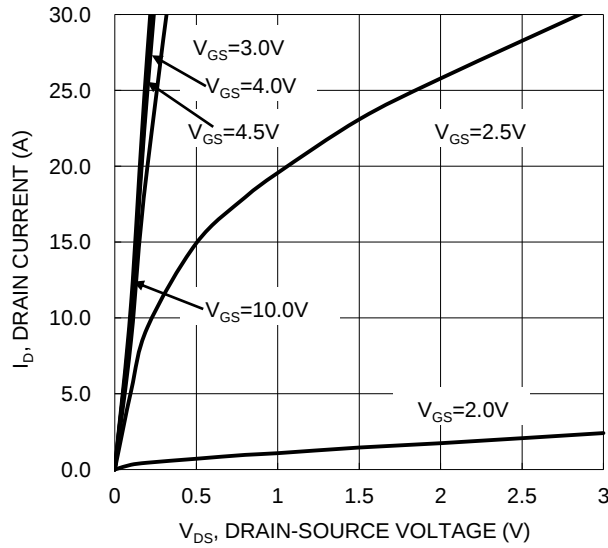


Figure 1. Typical Output Characteristic

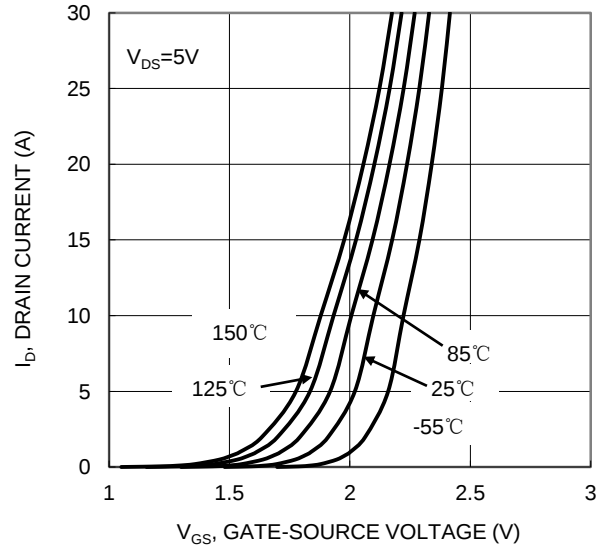


Figure 2. Typical Transfer Characteristic

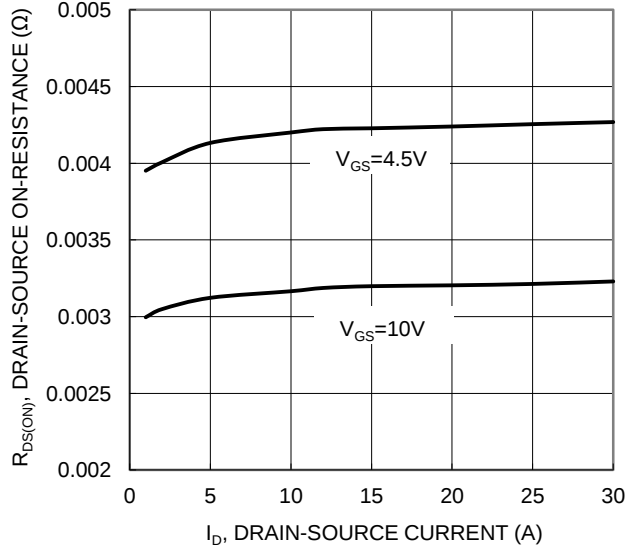


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

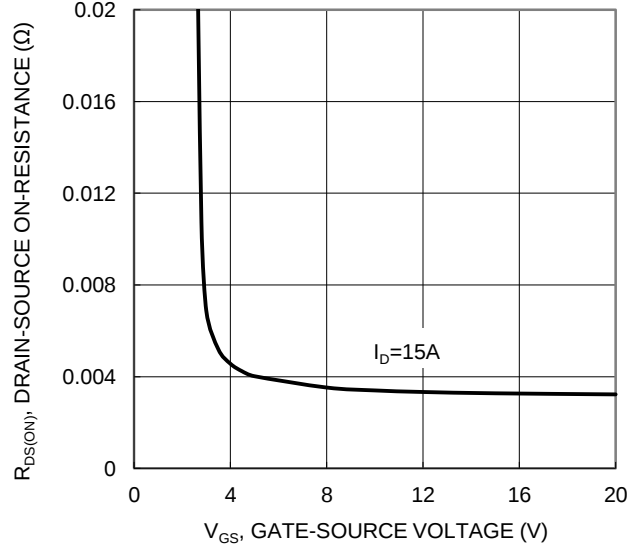


Figure 4. Typical Transfer Characteristic

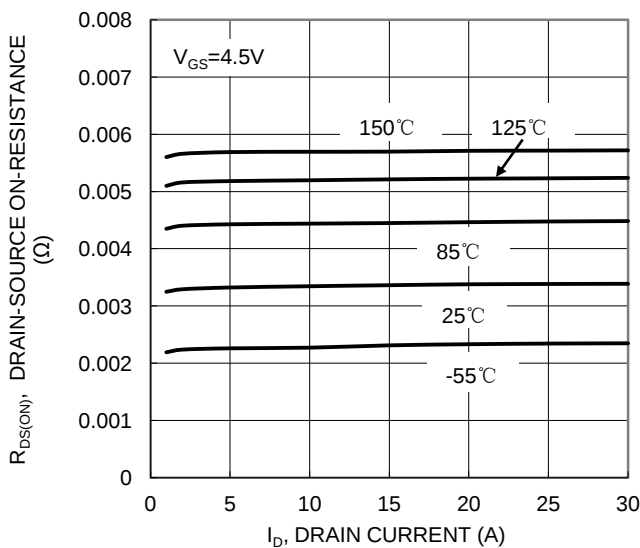


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

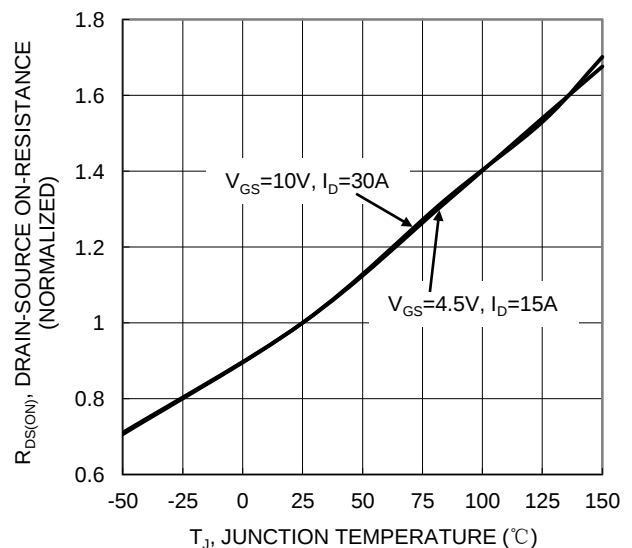


Figure 6. On-Resistance Variation with Temperature

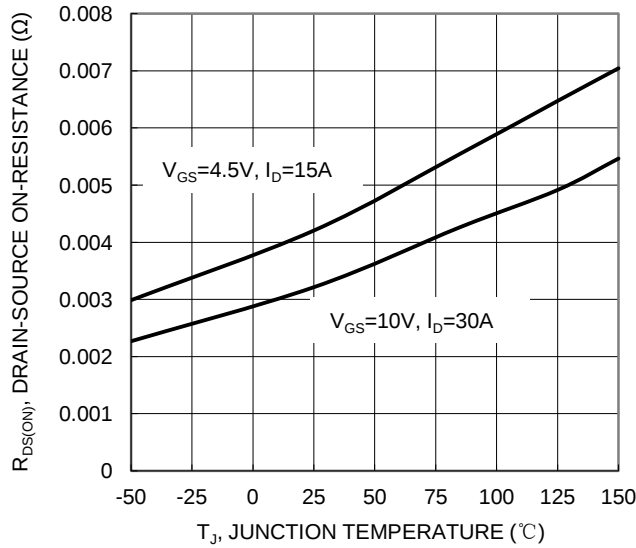


Figure 7. On-Resistance Variation with Temperature

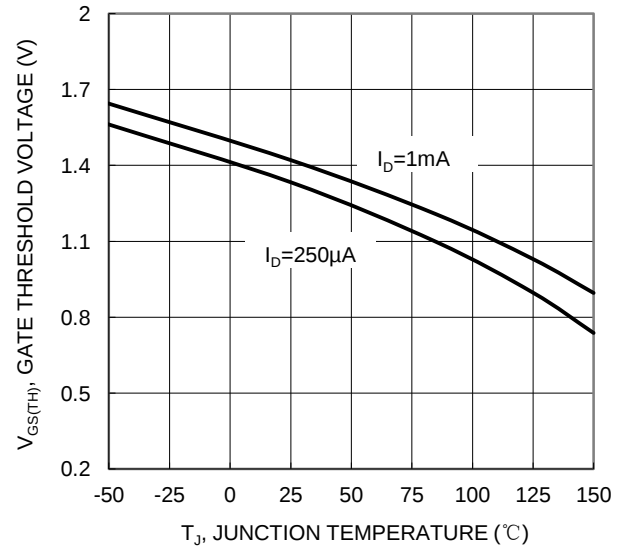


Figure 8. Gate Threshold Variation vs. Junction Temperature

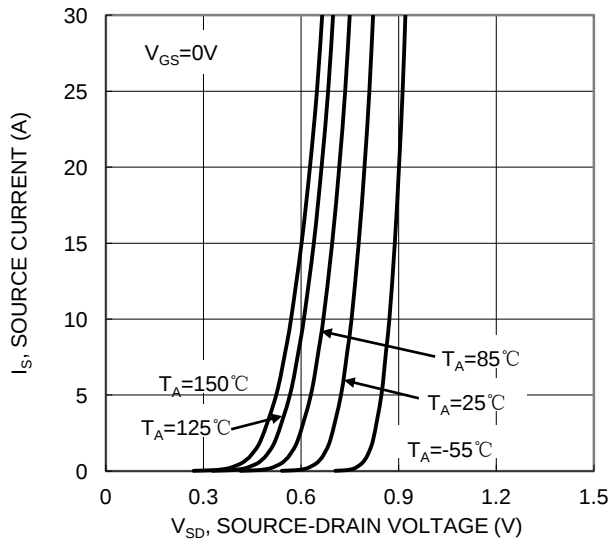


Figure 9. Diode Forward Voltage vs. Current

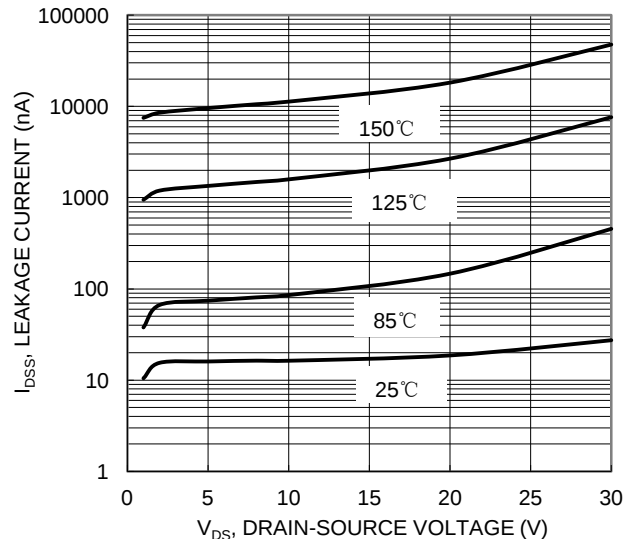


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

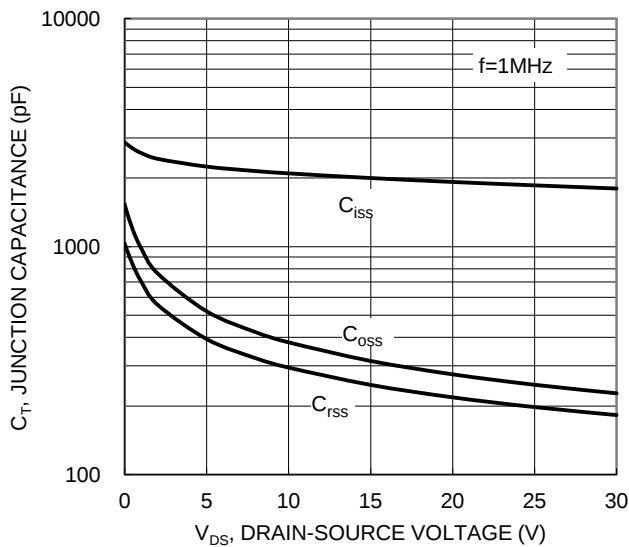


Figure 11. Typical Junction Capacitance

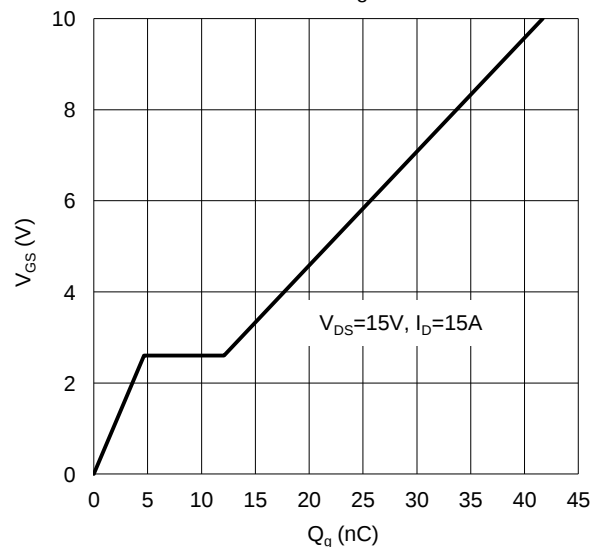
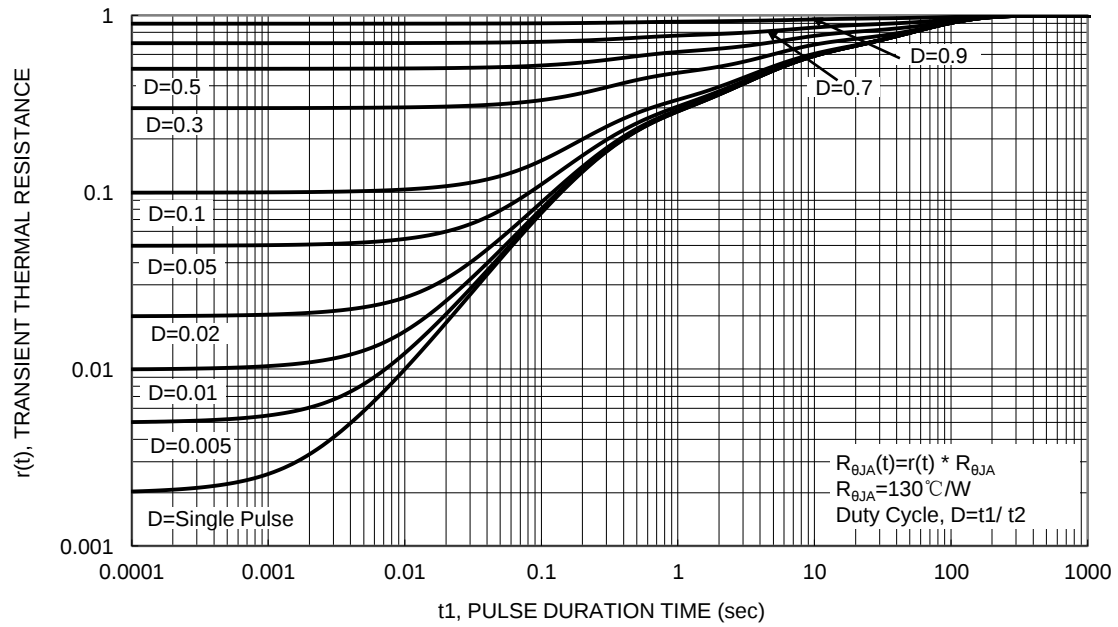
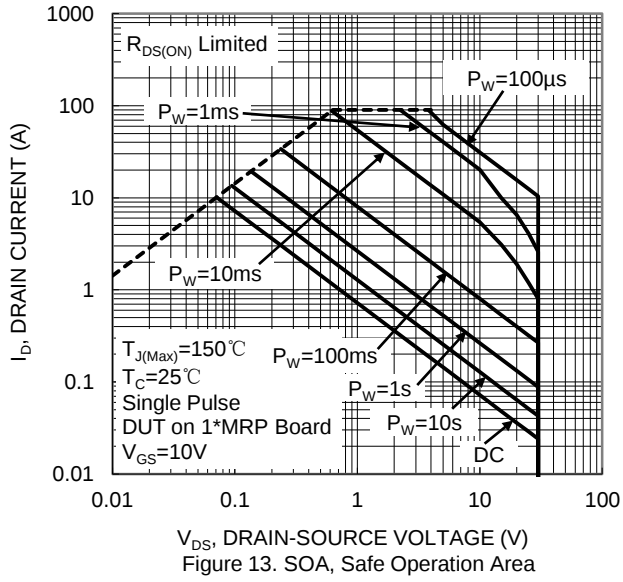


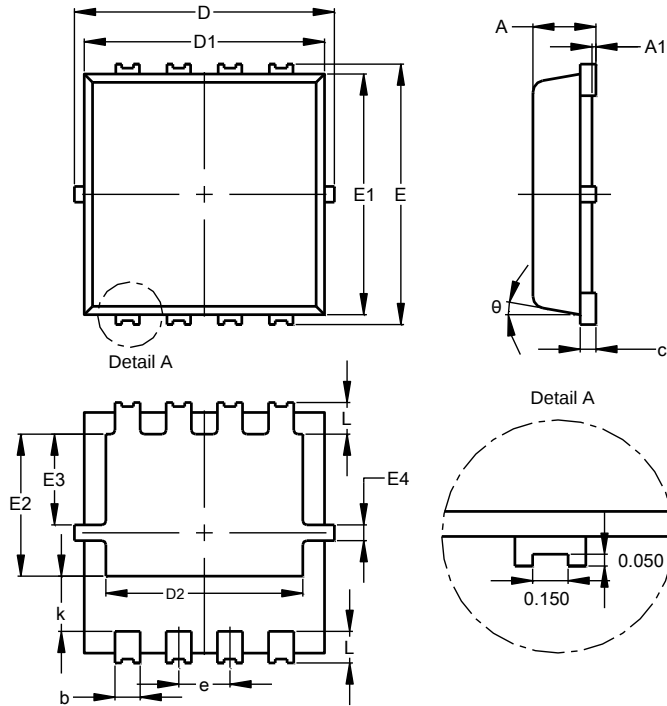
Figure 12. Gate Charge



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (SWP) (Type UX)

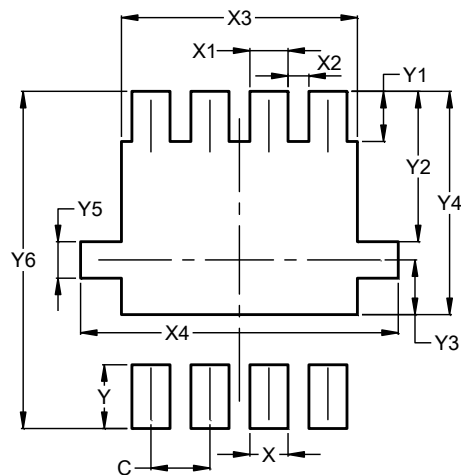


PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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